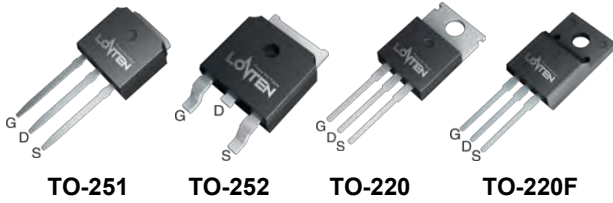
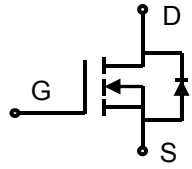


Lonten N-channel 650V, 5A Power MOSFET

<p>Description</p> <p>The Power MOSFET is fabricated using the advanced planar VDMOS technology. The resulting device has low conduction resistance, superior switching performance and high avalanche energy.</p> <p>Features</p> <ul style="list-style-type: none"> ◆ Low $R_{DS(on)}$ ◆ Low gate charge (typ. $Q_g = 14.5$ nC) ◆ 100% UIS tested ◆ RoHS compliant <p>Applications</p> <ul style="list-style-type: none"> ◆ Power factor correction. ◆ Switched mode power supplies. ◆ LED driver. 	<p>Product Summary</p> <table> <tr> <td>V_{DSS}</td> <td>650V</td> </tr> <tr> <td>I_D</td> <td>5A</td> </tr> <tr> <td>$R_{DS(on),max}$</td> <td>2.1Ω</td> </tr> <tr> <td>$Q_{g,typ}$</td> <td>14.5 nC</td> </tr> </table> <div style="text-align: center;">  <p>TO-251 TO-252 TO-220 TO-220F</p> </div> <div style="text-align: center;">  <p>N-Channel MOSFET</p> </div>	V_{DSS}	650V	I_D	5A	$R_{DS(on),max}$	2.1 Ω	$Q_{g,typ}$	14.5 nC
V_{DSS}	650V								
I_D	5A								
$R_{DS(on),max}$	2.1 Ω								
$Q_{g,typ}$	14.5 nC								

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	650	V
Continuous drain current ($T_C = 25^\circ\text{C}$)	I_D	5	A
($T_C = 100^\circ\text{C}$)		3.1	A
Pulsed drain current ¹⁾	I_{DM}	20	A
Gate-Source voltage	V_{GSS}	± 30	V
Avalanche energy, single pulse ²⁾	E_{AS}	245	mJ
Peak diode recovery dv/dt ³⁾	dv/dt	5	V/ns
Power Dissipation TO-220F ($T_C = 25^\circ\text{C}$)	P_D	30	W
Derate above 25°C		0.24	W/ $^\circ\text{C}$
Power Dissipation TO-220\TO-251\TO-252 ($T_C = 25^\circ\text{C}$)	P_D	75	W
Derate above 25°C		0.6	W/ $^\circ\text{C}$
Operating junction and storage temperature range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$
Continuous diode forward current	I_S	5	A
Diode pulse current	$I_{S,pulse}$	20	A

Thermal Characteristics

Parameter	Symbol	Value		Unit
		TO-220F	TO-220\TO-251\TO-252	
Thermal resistance, Junction-to-case	$R_{\theta JC}$	4.17	1.67	$^\circ\text{C}/\text{W}$
Thermal resistance, Junction-to-ambient	$R_{\theta JA}$	62.5	110	$^\circ\text{C}/\text{W}$

Package Marking and Ordering Information

Device	Device Package	Marking	Units/Tube	Units/Reel
LNC5N65B	TO-220	LNC5N65B	50	
LND5N65B	TO-220F	LND5N65B	50	
LNG5N65B	TO-252	LNG5N65B		3000
LNH5N65B	TO-251	LNH5N65B	80	

Electrical Characteristics T_c = 25°C unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static characteristics						
Drain-source breakdown voltage	BV _{DSS}	V _{GS} =0 V, I _D =0.25 mA	650	-	-	V
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =0.25 mA	2	-	4	V
Drain cut-off current	I _{DSS}	V _{DS} =650 V, V _{GS} =0 V, T _J = 25°C T _J = 125°C	-	-	1 100	μA
Gate leakage current, Forward	I _{GSSF}	V _{GS} =30 V, V _{DS} =0 V	-	-	100	nA
Gate leakage current, Reverse	I _{GSSR}	V _{GS} =-30 V, V _{DS} =0 V	-	-	-100	nA
Drain-source on-state resistance	R _{DS(on)}	V _{GS} =10 V, I _D =2.5 A	-	1.8	2.1	Ω
Dynamic characteristics						
Input capacitance	C _{iss}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz	-	730	-	pF
Output capacitance	C _{oss}		-	60	-	
Reverse transfer capacitance	C _{rss}		-	3.5	-	
Turn-on delay time	t _{d(on)}	V _{DD} = 325 V, I _D = 5 A R _G = 10 Ω, V _{GS} =15 V	-	12.2	-	ns
Rise time	t _r		-	35	-	
Turn-off delay time	t _{d(off)}		-	35	-	
Fall time	t _f		-	14.8	-	
Gate charge characteristics						
Gate to source charge	Q _{gs}	V _{DD} =520 V, I _D =5 A, V _{GS} =0 to 10 V	-	4.3	-	nC
Gate to drain charge	Q _{gd}		-	5.3	-	
Gate charge total	Q _g		-	14.5	-	
Gate plateau voltage	V _{plateau}		-	5	-	V
Reverse diode characteristics						
Diode forward voltage	V _{SD}	V _{GS} =0 V, I _F =5 A	-	-	1.3	V
Reverse recovery time	t _{rr}	V _R =520 V, I _F =5 A, di _F /dt=100 A/μs	-	340	-	ns
Reverse recovery charge	Q _{rr}		-	2.09	-	μC
Peak reverse recovery current	I _{rrm}		-	12.3	-	A

Notes:

- Pulse width limited by maximum junction temperature.
- L=10mH, I_{AS} = 7A, Starting T_J= 25°C.
- I_{SD} = 5A, di/dt≤100A/μs, V_{DD}≤BV_{DSS}, Starting T_J= 25°C.

Electrical Characteristics Diagrams

Figure 1. Typical Output Characteristics

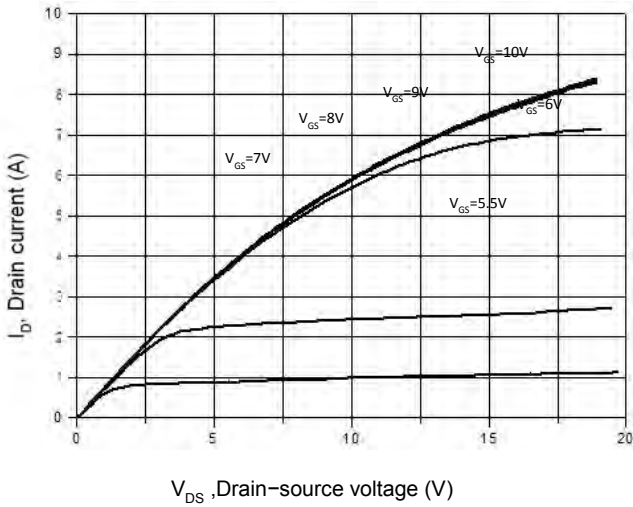


Figure 2. Transfer Characteristics

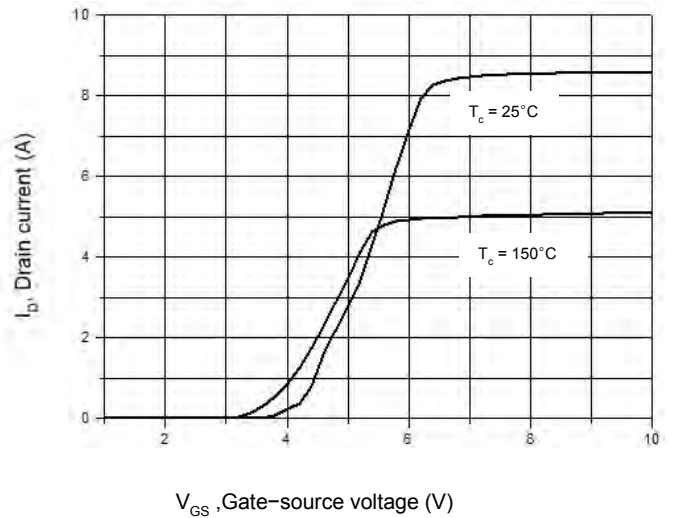


Figure 3. On-Resistance Variation vs. Drain Current

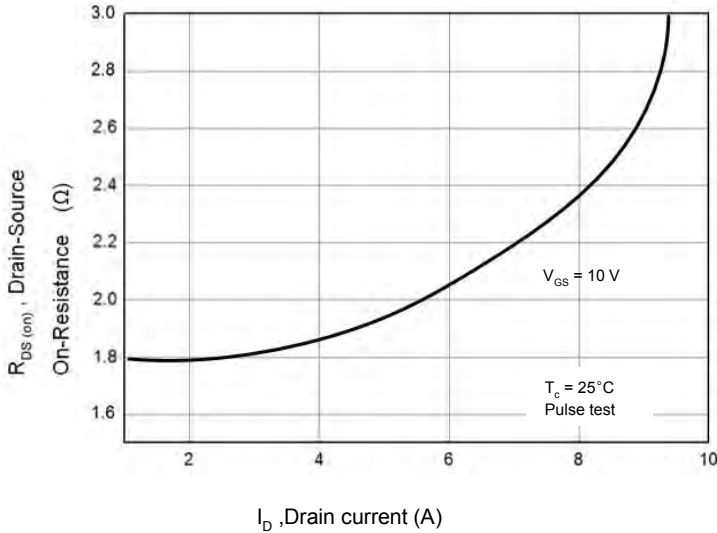


Figure 4. Threshold Voltage vs. Temperature

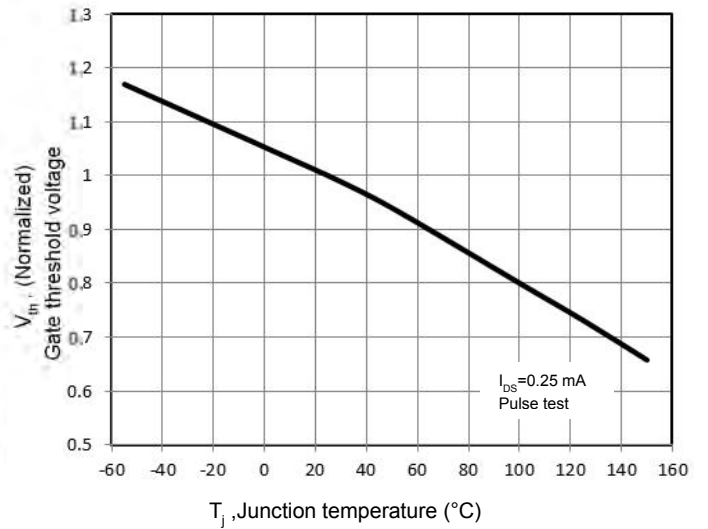


Figure 5. Breakdown Voltage vs. Temperature

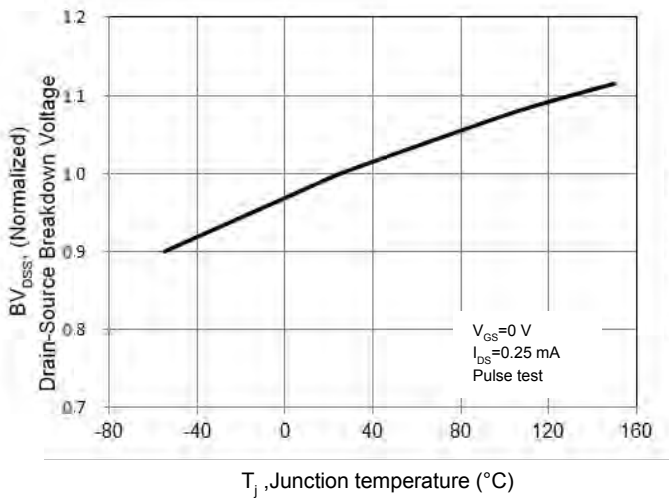


Figure 6. On-Resistance vs. Temperature

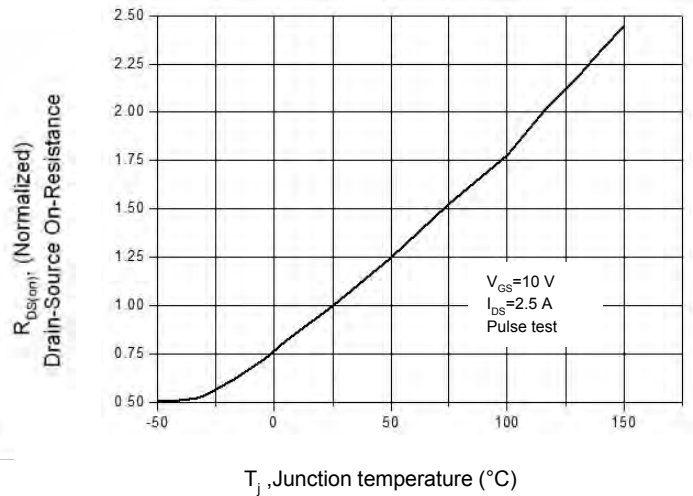


Figure 7. Capacitance Characteristics

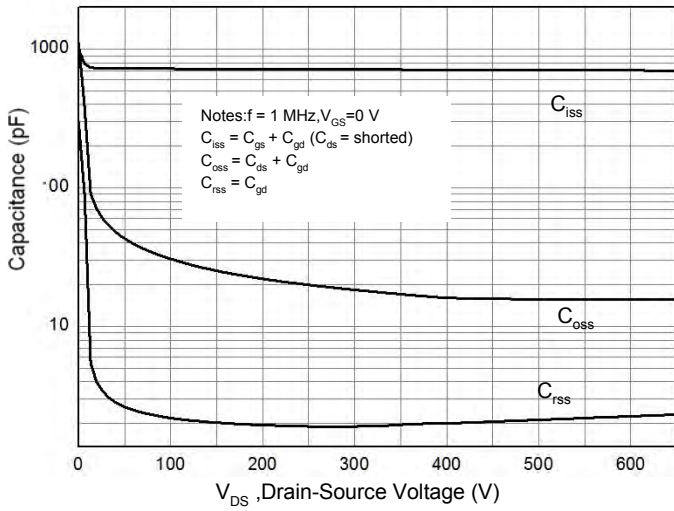


Figure 8. Gate Charge Characteristics

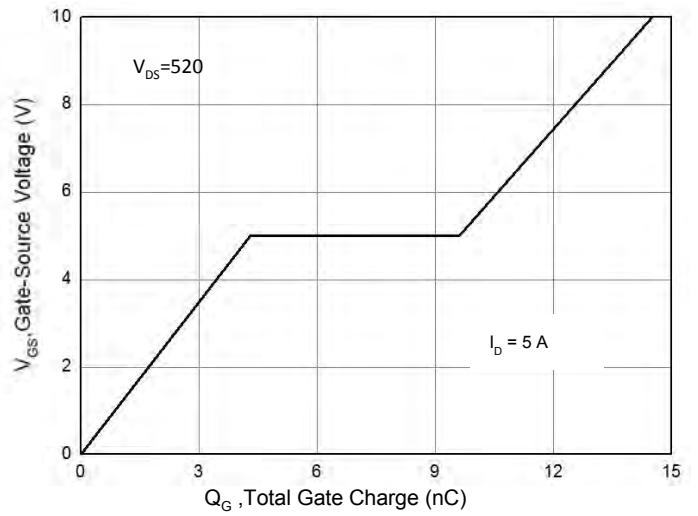


Figure 9. Maximum Safe Operating Area TO-220F

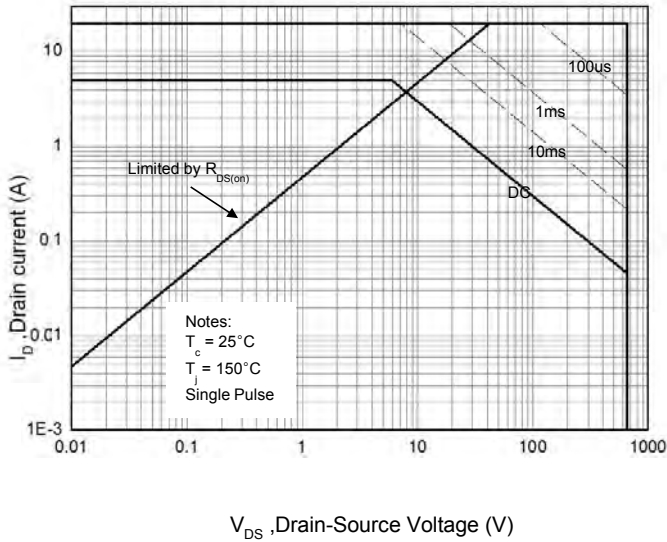


Figure 10. Maximum Safe Operating Area TO-220/TO-251/TO-252

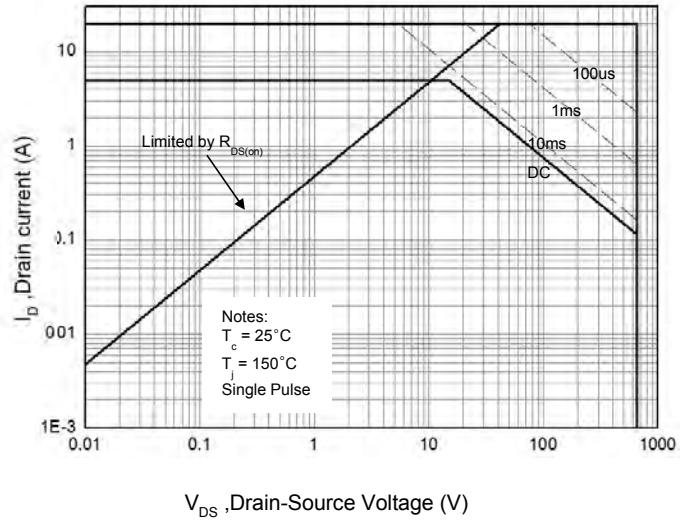


Figure 11. Power Dissipation vs. Temperature TO-220F

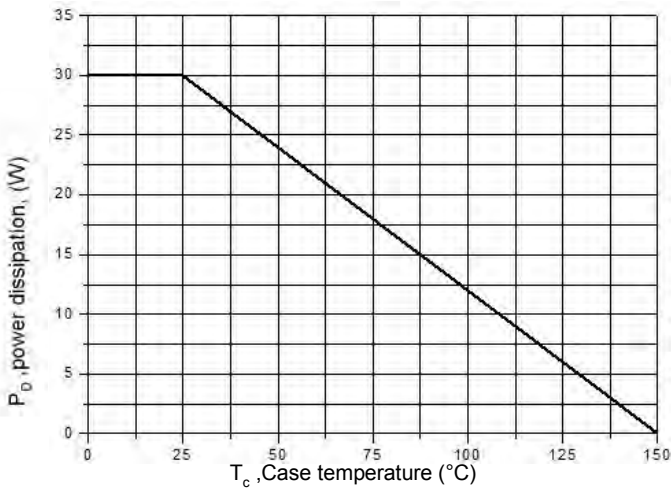


Figure 12. Power Dissipation vs. Temperature TO-220/TO-251/TO-252

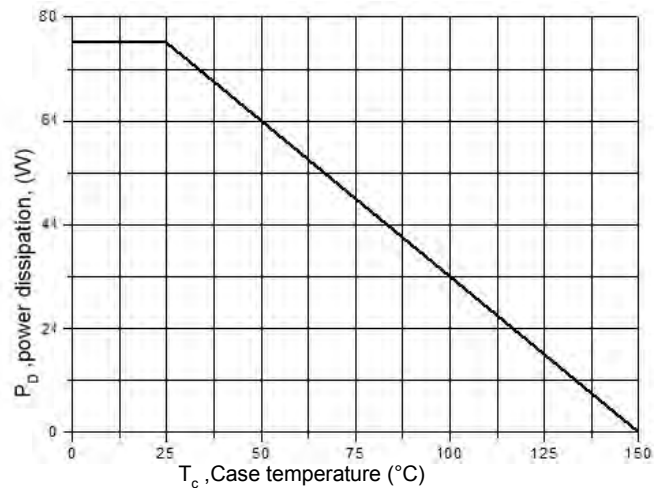
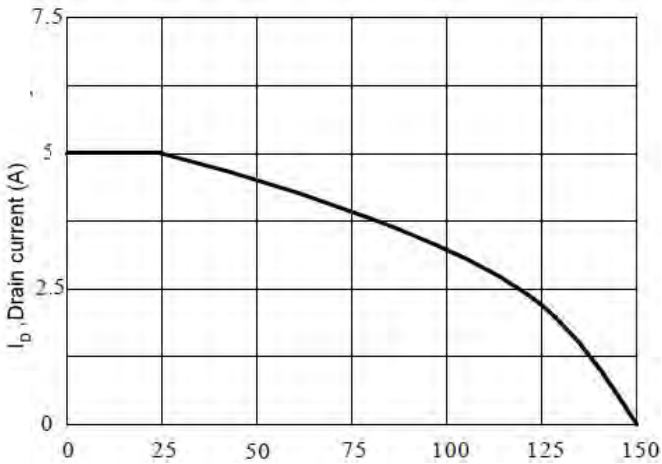
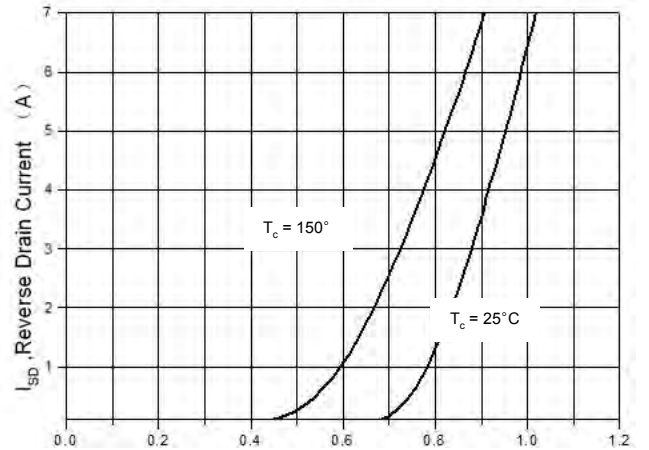


Figure 13. Continuous Drain Current vs. Temperature



T_c , Case temperature (°C)

Figure 14. Body Diode Transfer Characteristics



V_{SD} , Source-Drain Voltage (V)

Figure 15 Transient Thermal Impedance, Junction to Case, TO-220F

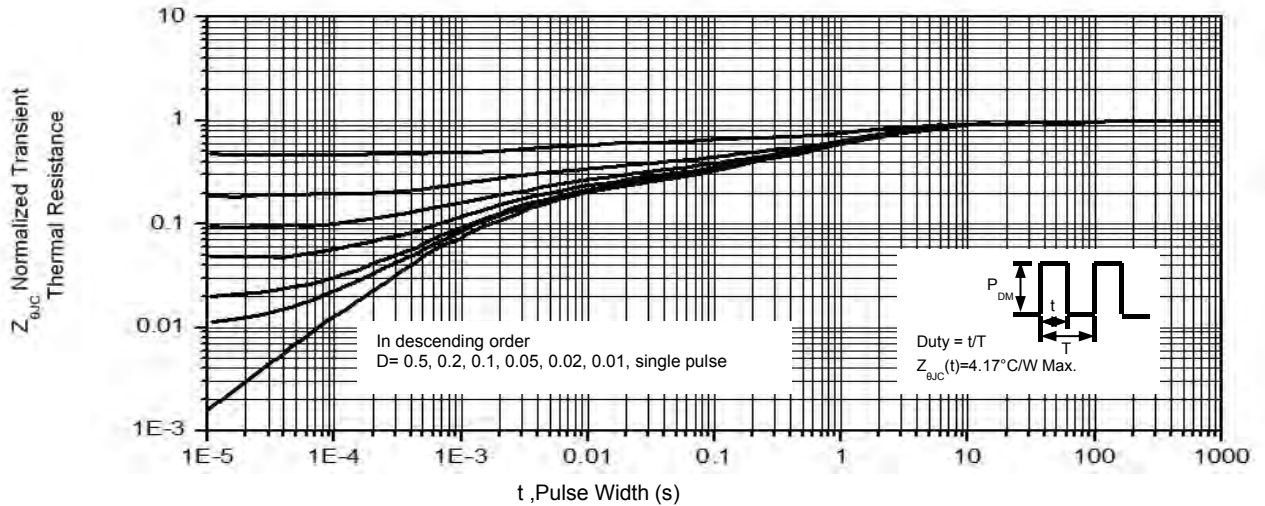
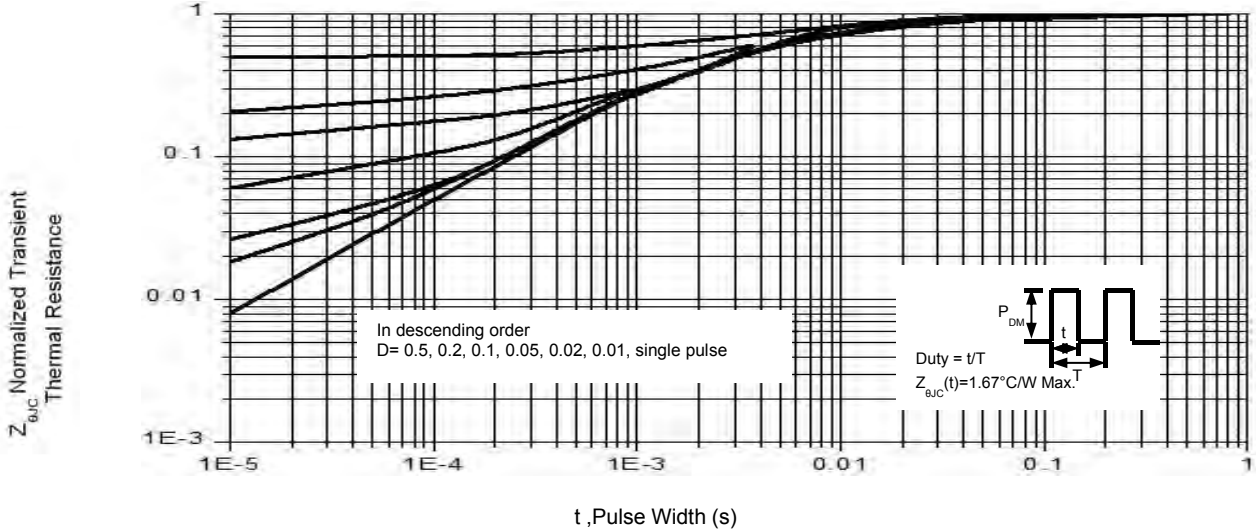
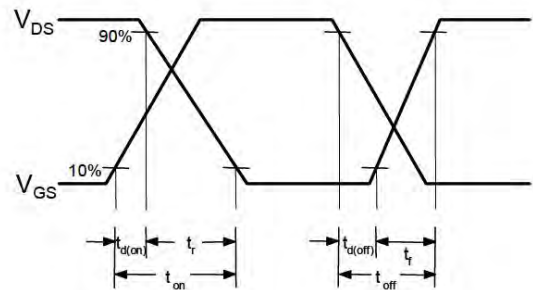
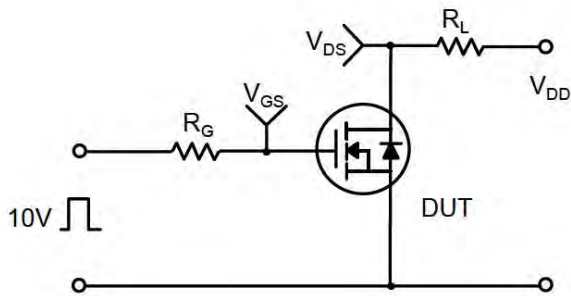
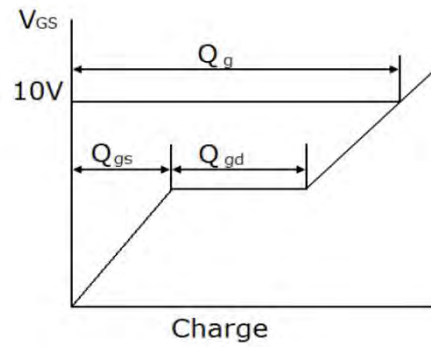
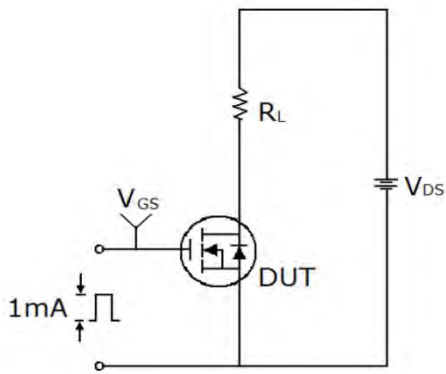


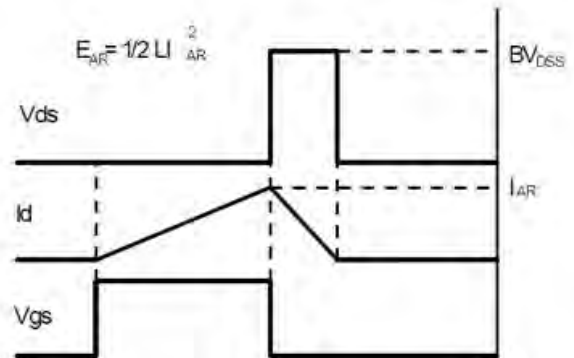
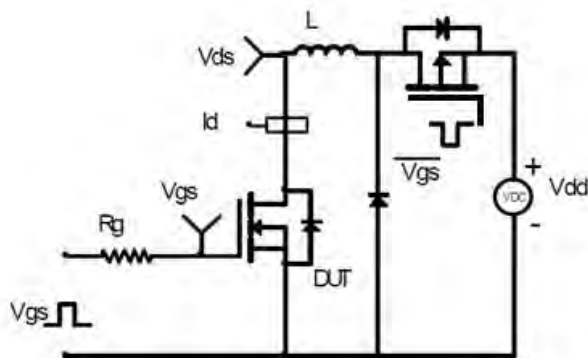
Figure 16. Transient Thermal Impedance, Junction to Case, TO-220/TO-251/TO-252



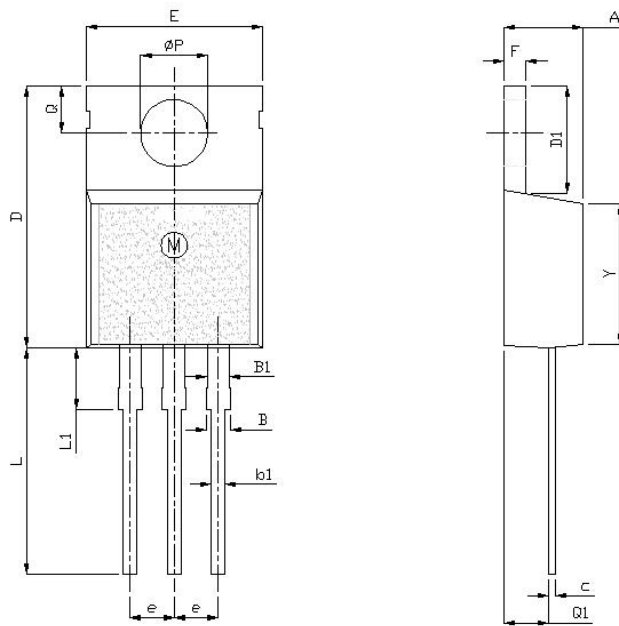
Gate Charge Test Circuit & Waveform



Unclamped Inductive Switching Test Circuit & Waveforms



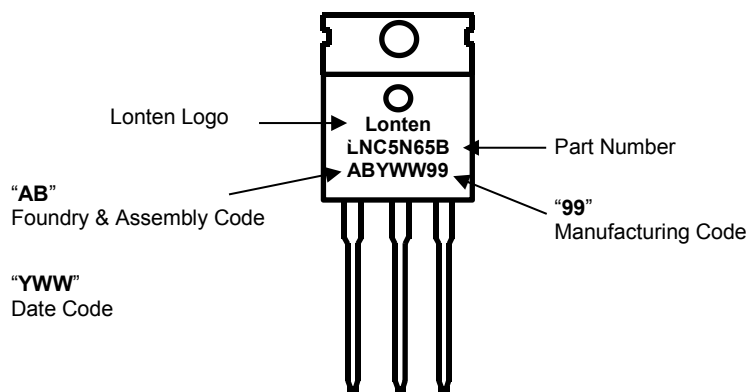
Mechanical Dimensions for TO-220



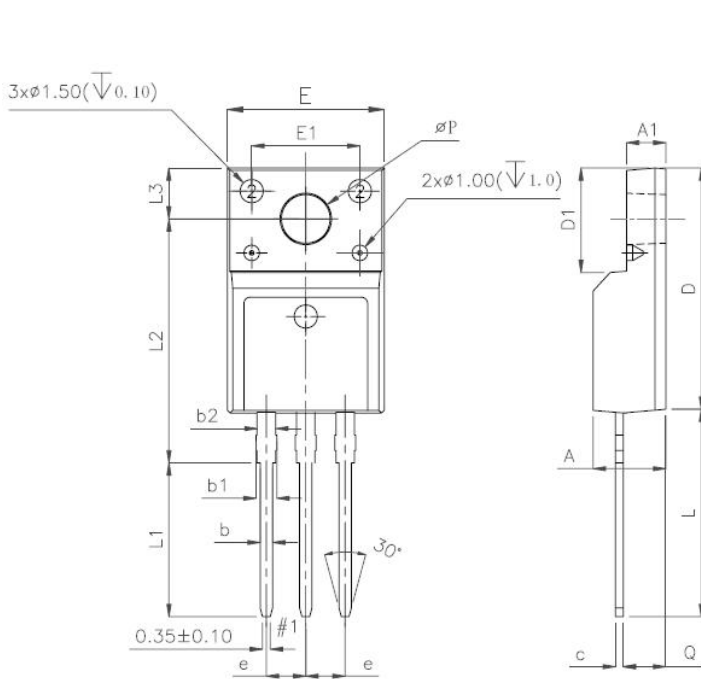
UNIT: mm

SYMBOL	MIN	NOM	MAX
A	4		4.8
B	1.2		1.4
B1	1		1.4
b1	0.75		0.95
c	0.4		0.55
D	15		16.5
D1	5.9		6.9
E	9.9		10.7
e	2.44	2.54	2.64
F	1.1		1.4
L	12.5		14.5
L1	3	3.5	4
ϕP	3.7	3.8	3.9
Q	2.5		3
Q1	2		2.9
Y	8.02	8.12	8.22

TO-220 Part Marking Information



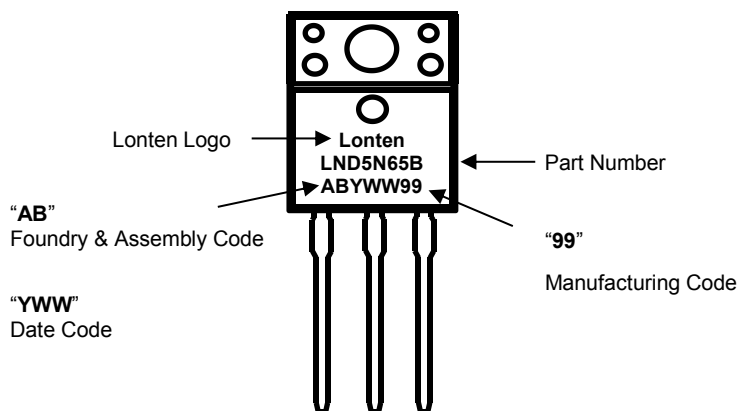
Mechanical Dimensions for TO-220F



UNIT: mm

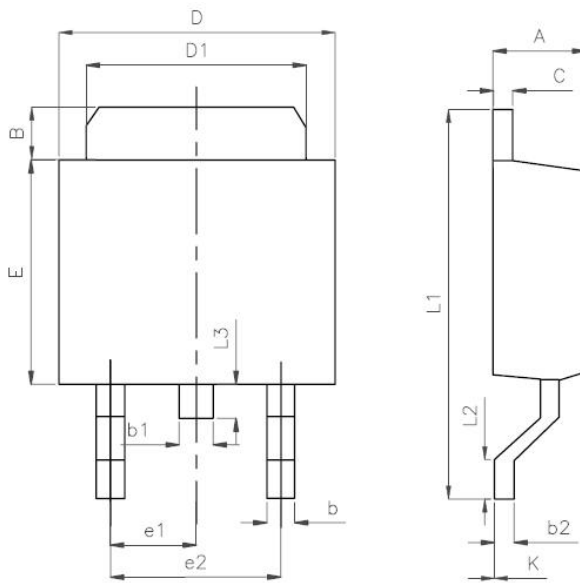
SYMBOL	MIN	NOM	MAX
A	4.5		4.9
A1	2.3		2.9
b	0.65		0.9
b1	1.1		1.7
b2	1.2		1.4
c	0.35		0.65
D	14.5		16.5
D1	6.1		6.9
E	9.6		10.3
E1	6.5	7	7.5
e	2.44	2.54	2.64
L	12.5		14.3
L1	9.45		10.05
L2	15		16
L3	3.2		4.4
ϕP	3		3.3
Q	2.5		2.9

TO-220F Part Marking Information



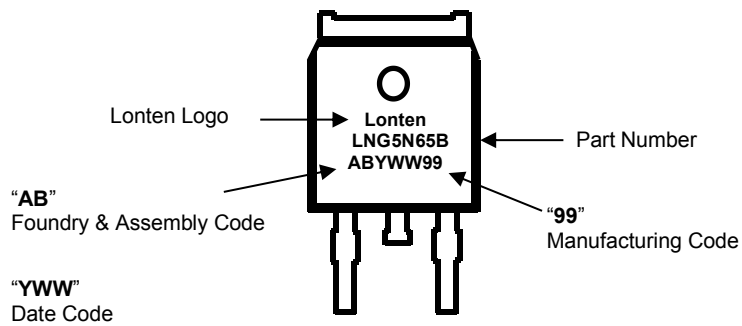
Mechanical Dimensions for TO-252

UNIT: mm



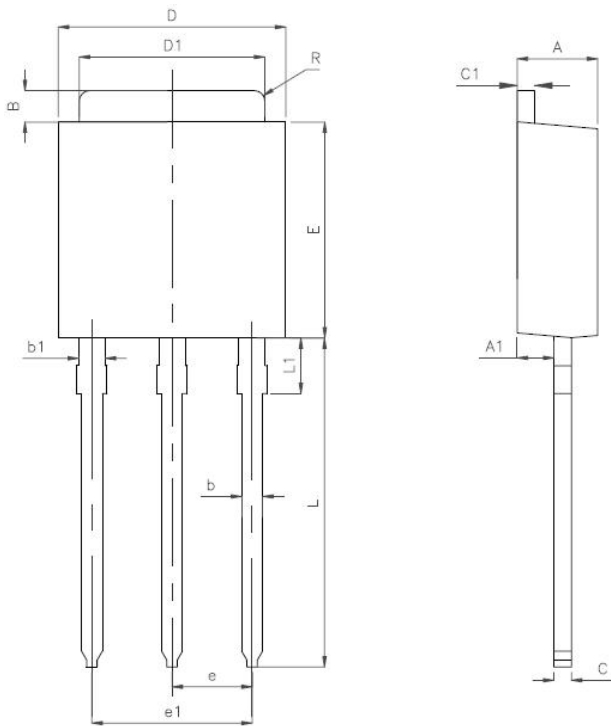
SYMBOL	MIN	NOM	MAX
A	2.10		2.50
B	0.80		1.25
b	0.50		0.85
b1	0.50		0.90
b2	0.45		0.60
C	0.45		0.60
D	6.35		6.75
D1	5.10		5.50
E	5.80		6.30
e1	2.25	2.30	2.35
e2	4.45		4.75
L1	9.50		10.20
L2	0.90		1.45
L3	0.60		1.10
K	-0.1		0.10

TO-252 Part Marking Information



Mechanical Dimensions for TO-251

UNIT: mm



SYMBOL	MIN	NOM	MAX
A	2.10		2.50
A1	0.95		1.30
B	0.80		1.25
b	0.50		0.80
b1	0.70		0.90
C	0.45		0.60
C1	0.45		0.60
D	6.35		6.75
D1	5.10		5.50
E	5.80		6.30
e	2.25	2.30	2.35
L	7.70		8.50
L1	1.45		1.95
R		0.30	

TO-251 Part Marking Information

